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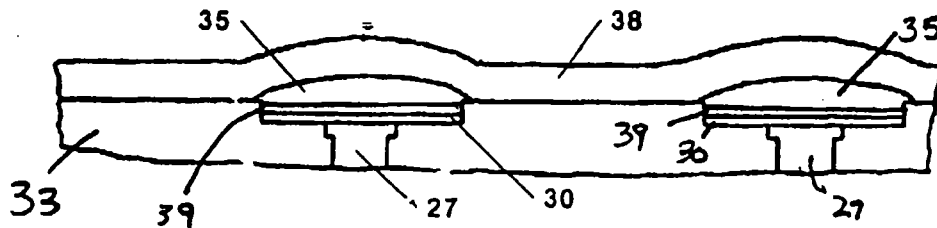
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ACTION

(54) Title: A MEMORY DEVICE WITH A SELF-ASSEMBLED POLYMER FILM AND METHOD OF MAKING THE SAME



(57) Abstract: A memory device with multi-bit memory cells and method of making the same uses self-assembly to provide polymer memory cells on the contacts to a transistor array. Employing self-assembly produces polymer memory cells at the precise locations of the contacts of the transistor array. The polymer memory cells change resistance values in response to electric current above a specified threshold value. The memory cells retain the resistivity values over time.

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